

# MMBT4403WT1

## Switching Transistor

### PNP Silicon

#### Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV,  
Machine Model; 400 V
- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–600	mAdc

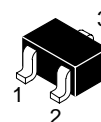
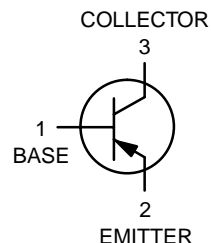
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$



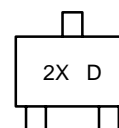
**ON Semiconductor®**

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SC–70  
CASE 419  
STYLE 3

#### MARKING DIAGRAM



2X = Specific Device Code  
D = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT4403WT1	SC–70	3000/Tape & Reel
MMBT4403WT1G	SC–70 (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT4403WT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 1) ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-40	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = -0.1\text{ mA}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-40	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -0.1\text{ mA}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	–	Vdc
Base Cutoff Current ( $V_{CE} = -35\text{ Vdc}$ , $V_{EB} = -0.4\text{ Vdc}$ )	$I_{BEV}$	–	-0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = -35\text{ Vdc}$ , $V_{EB} = -0.4\text{ Vdc}$ )	$I_{CEX}$	–	-0.1	$\mu\text{Adc}$

## ON CHARACTERISTICS

DC Current Gain ( $I_C = -0.1\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -150\text{ mA}$ , $V_{CE} = -2.0\text{ Vdc}$ ) (Note 1) ( $I_C = -500\text{ mA}$ , $V_{CE} = -2.0\text{ Vdc}$ ) (Note 1)	$h_{FE}$	30 60 100 100 20	– – – 300 –	–
Collector–Emitter Saturation Voltage (Note 1) ( $I_C = -150\text{ mA}$ , $I_B = -15\text{ mA}$ ) ( $I_C = -500\text{ mA}$ , $I_B = -50\text{ mA}$ )	$V_{CE(sat)}$	– –	-0.4 -0.75	Vdc
Base–Emitter Saturation Voltage (Note 1) ( $I_C = -150\text{ mA}$ , $I_B = -15\text{ mA}$ ) ( $I_C = -500\text{ mA}$ , $I_B = -50\text{ mA}$ )	$V_{BE(sat)}$	-0.75 –	-0.95 -1.3	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ( $I_C = -20\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	200	–	MHz
Collector–Base Capacitance ( $V_{CB} = -10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	–	8.5	pF
Emitter–Base Capacitance ( $V_{BE} = -0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{eb}$	–	30	pF
Input Impedance ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	1.5	15	k $\Omega$
Voltage Feedback Ratio ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	0.1	8.0	$\times 10^{-4}$
Small–Signal Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	60	500	–
Output Admittance ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	1.0	100	$\mu\text{mhos}$

## SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = -30\text{ Vdc}$ , $V_{EB} = -2.0\text{ Vdc}$ , $I_C = -150\text{ mA}$ , $I_{B1} = -15\text{ mA}$ )	$t_d$	–	15	ns
Rise Time		$t_r$	–	20	
Storage Time	$(V_{CC} = -30\text{ Vdc}$ , $I_C = -150\text{ mA}$ , $I_{B1} = I_{B2} = -15\text{ mA}$ )	$t_s$	–	225	ns
Fall Time		$t_f$	–	30	

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

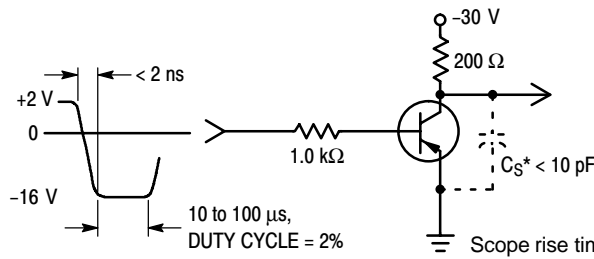


Figure 1. Turn–On Time

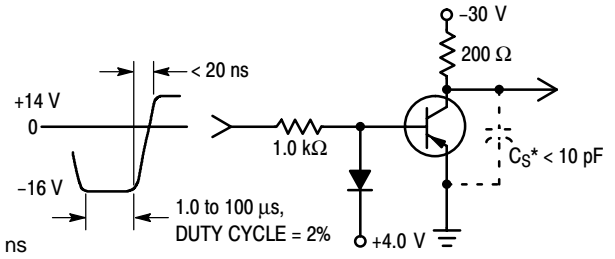


Figure 2. Turn–Off Time

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## TRANSIENT CHARACTERISTICS

— 25°C — 100°C

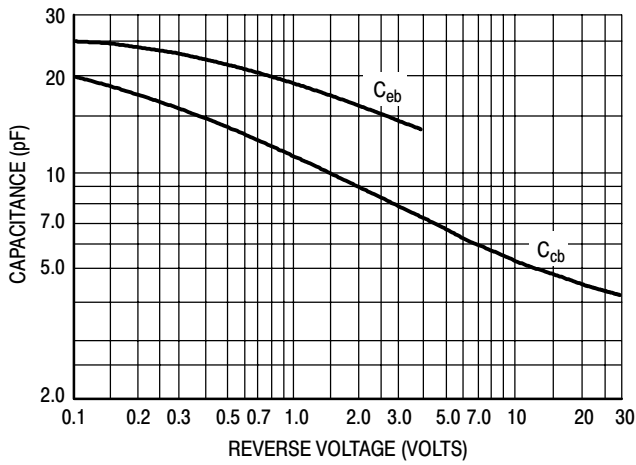


Figure 3. Capacitances

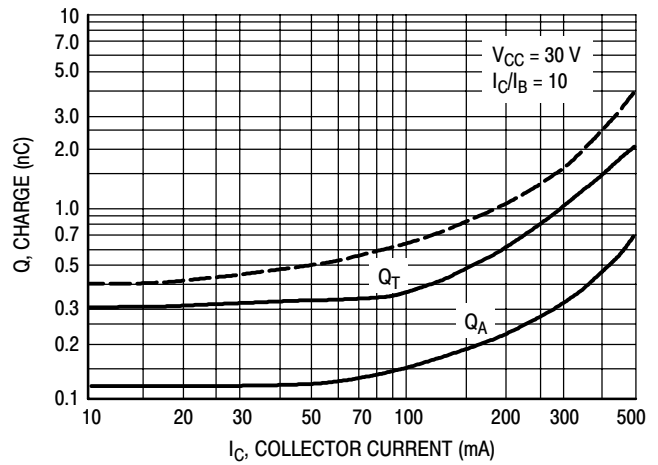


Figure 4. Charge Data

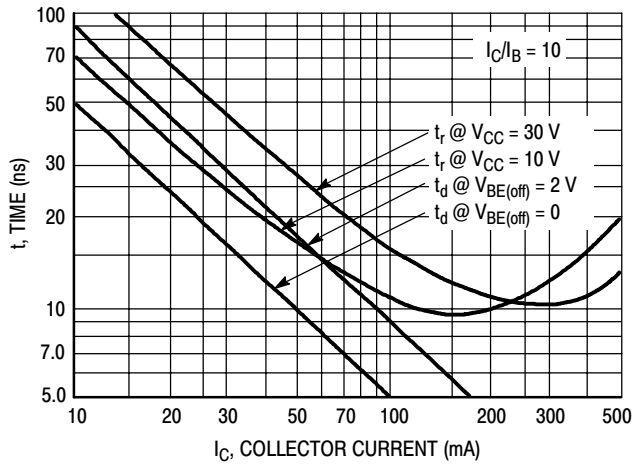


Figure 5. Turn-On Time

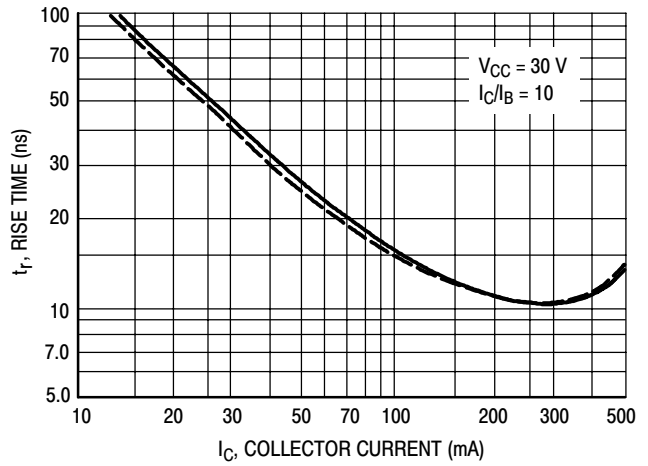


Figure 6. Rise Time

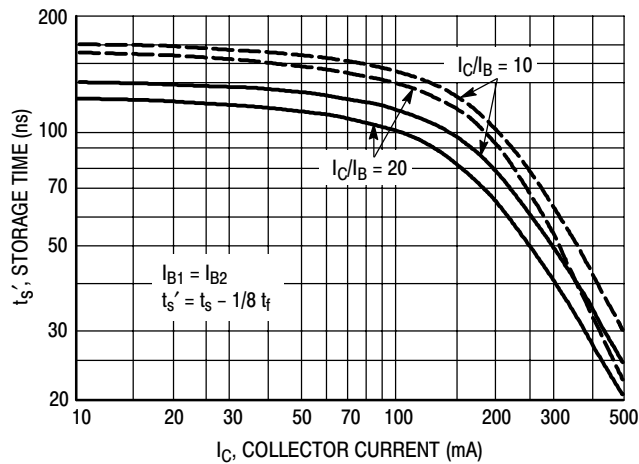


Figure 7. Storage Time

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## SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ ; Bandwidth = 1.0 Hz

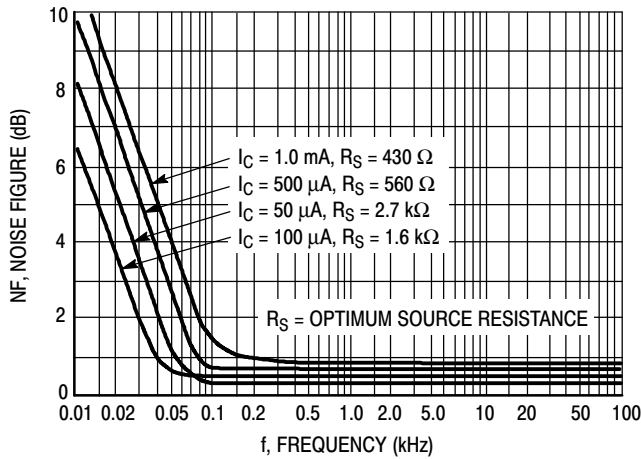


Figure 8. Frequency Effects

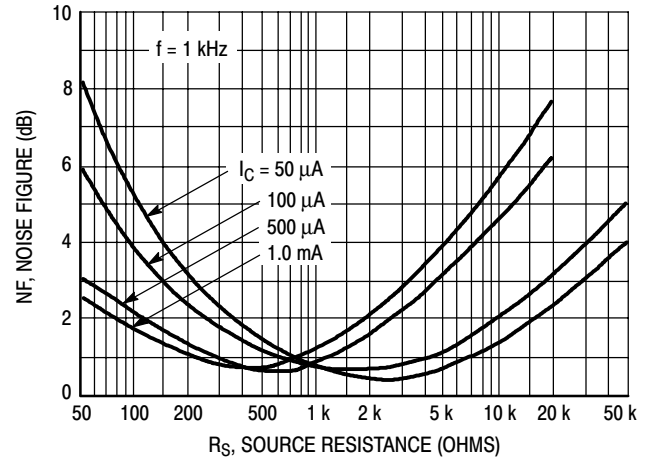


Figure 9. Source Resistance Effects

## h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

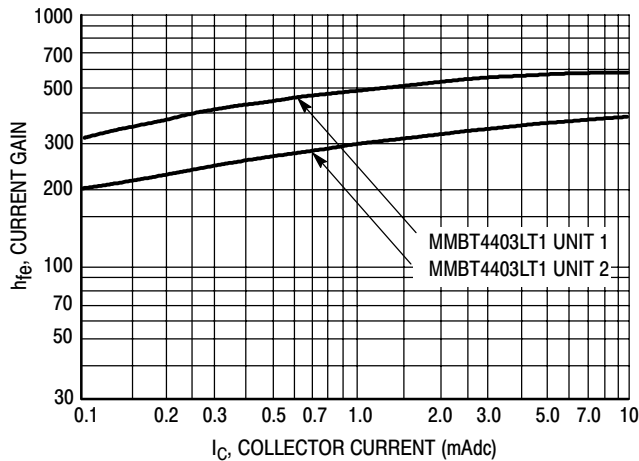


Figure 10. Current Gain

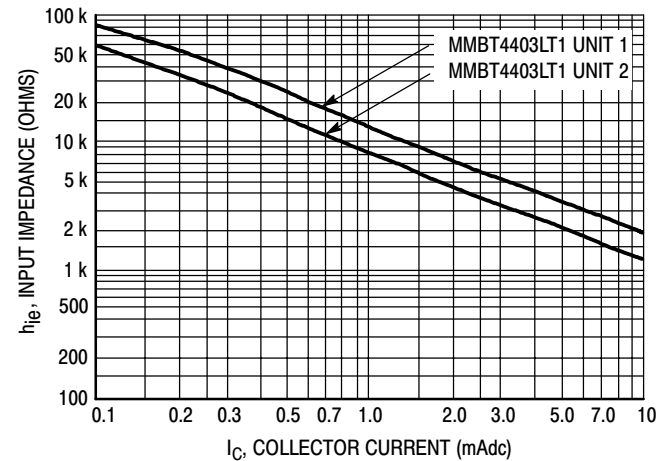


Figure 11. Input Impedance

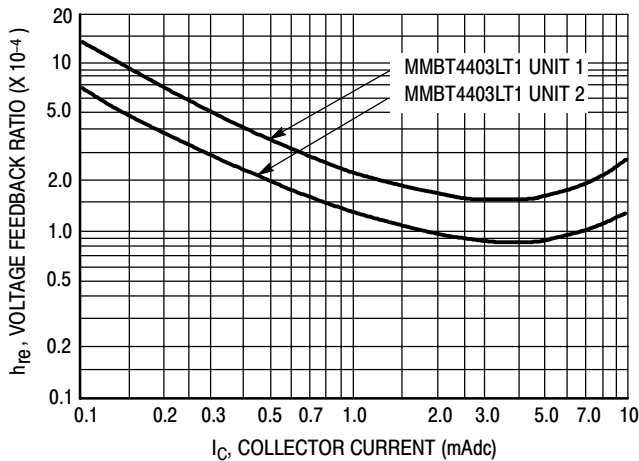


Figure 12. Voltage Feedback Ratio

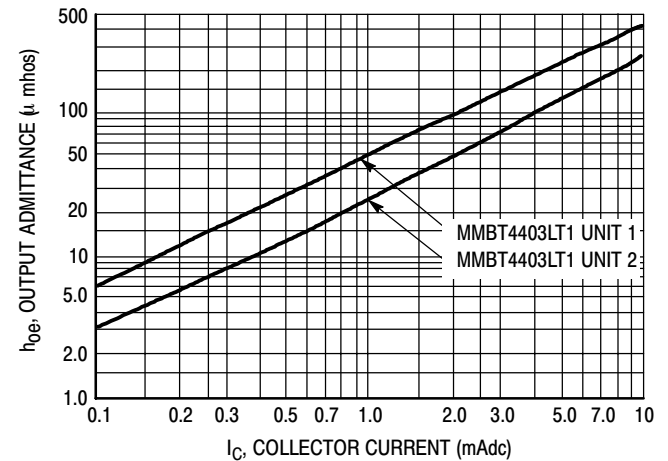


Figure 13. Output Admittance

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## STATIC CHARACTERISTICS

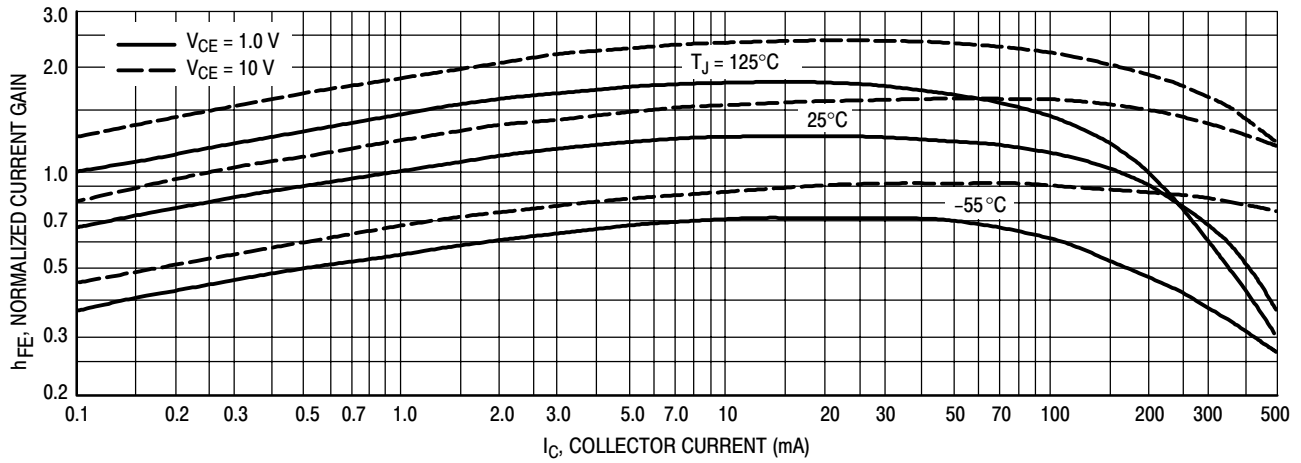


Figure 14. DC Current Gain

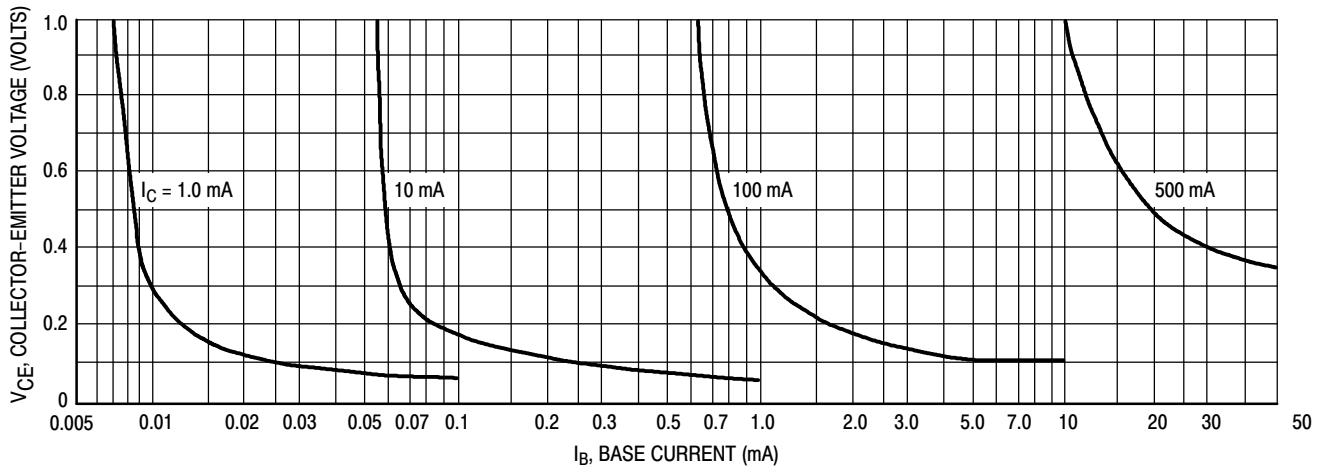


Figure 15. Collector Saturation Region

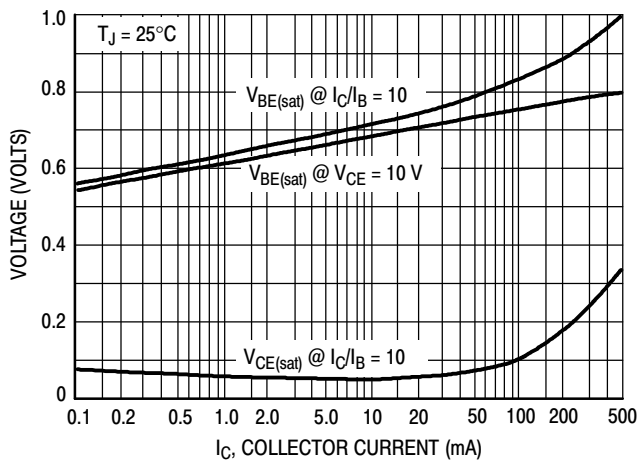


Figure 16. "On" Voltages

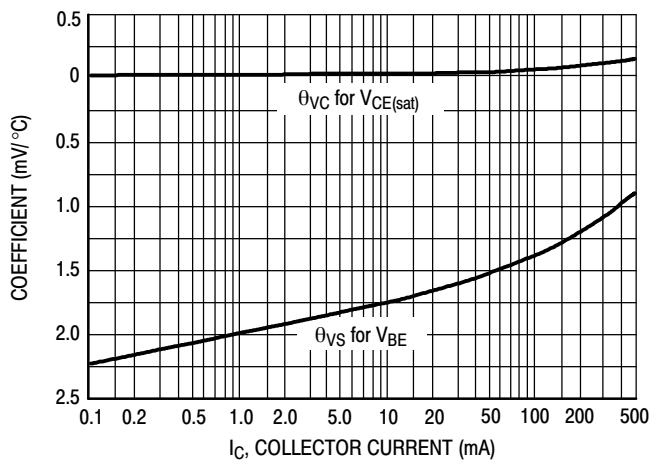
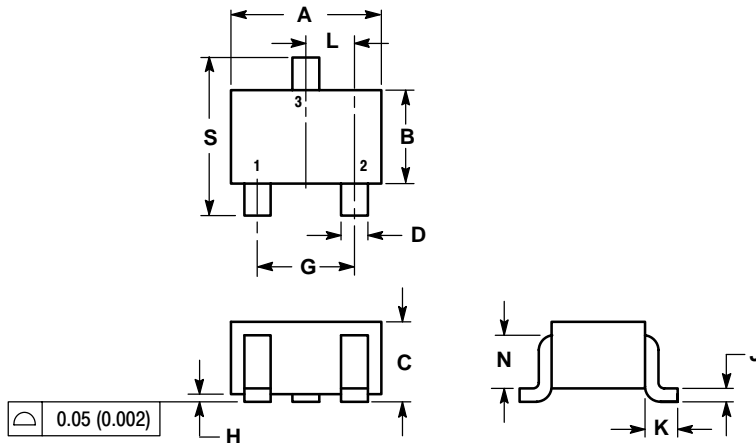


Figure 17. Temperature Coefficients

# MMBT4403WT1

## PACKAGE DIMENSIONS

### SC-70/SOT-323 CASE 419-04 ISSUE L



#### NOTES:

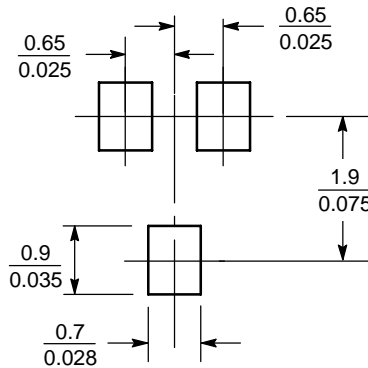
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017	REF	0.425	REF
L	0.026	BSC	0.650	BSC
N	0.028	REF	0.700	REF
S	0.079	0.095	2.00	2.40

#### STYLE 3:

- PIN 1. BASE
- EMITTER
- COLLECTOR


### SOLDERING FOOTPRINT\*



SCALE 10:1 (mm/inches)

### SC-70/SOT-323

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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